

IN THE SPECIFICATION:

1. On Page 6 of the specification, change the paragraph starting at line 20 as follows:

--Preferably, the first semiconductor layer is a Si layer, and the second semiconductor layer is a $\text{Si}_{1-x-y}\text{Ge}_x\text{C}_y$ layer ($0 < x < 1$, $0 \leq y \leq 1$). As a result, excellent characteristics can be obtained using a hetero junction.--

2. On Page 7 of the specification, change the paragraph starting at line 18 as follows:

--Preferably, the third and fourth semiconductor layers each including a $\text{Si}_{1-x-y}\text{Ge}_x\text{C}_y$ layer ($0 < x < 1$, $0 \leq y \leq 1$) are formed in the step (b). This enables formation of a semiconductor device including a bipolar transistor having excellent frequency characteristics and a variable capacitor having a large variation range of capacitance.--